

Semiconductor **E**quipment Assessment Leveraging Innovation



SEAL PROJECT - BULLETIN

SEAL SP3 - A2D2 Advanced Vacuum wafer Drying for TLS Dicing

AT A GLANCE Evaluation of а cleaning method for diced wafers Integration and assessment of vacuum drying module in a TLS dicing tool

PARTNERS adixen Vacuum Products Fraunhofer IISB Jenoptik Automatisierungstechnik

Advances in A2D2

Objectives: laser based wafer dicer, successfully demonstrated by Jenoptik, was enhanced with vacuum drying process to remove water residues from diced wafers (side effect of the TLS approach).

Activities performed:

- Definition of requirements for assessment
- A vacuum drying module was designed, prepared & manufactured
- Technical assessment was prepared & performed
- All developments done to have industrial prototype ready (mechanics; communication & electrics) and compatible with industrial assessment.
- Study of different industrial applications
- Dissemination including an international workshop



Figure 1: Calibrated droplets on various wafers /materials for frame and tape for experimental drying tests









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Project Results

- ➤ Vacuum drying module demonstrated as an efficient and competitive alternative for short drying process after TLS dicing step.
- ➤ Obtain a fully efficient, high quality and short clean drying process.
- ➤ Providing increased functionality, yield and separation of thinner and more flexible products and enhanced dicing speed.
- ➤ Various industrial applications identified.

SEAL PROJECT MANAGEMENT

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Figure 2: Versatile demonstrator for drying process.

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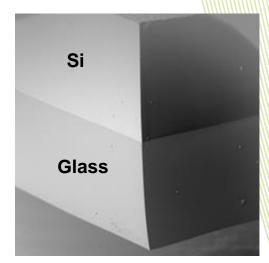


Figure 3: Topographic SEM images of exemplary TLS result (here: Si on glass with a total thickness of 950 µm) - smooth interface between silicon and glass, no chipping, no micro cracks.





